

- Q.2 a. In the circuit of Fig. 1,  $V_A = 2V$ ,  $I_A = 2A$ ,  $R_1 = 4\Omega$  and  $R_2 = 3\Omega$ . Find the Thevenin equivalent voltage  $V_{th}$  and impedance  $Z_{th}$  for the network to the left of terminals 1, 2.

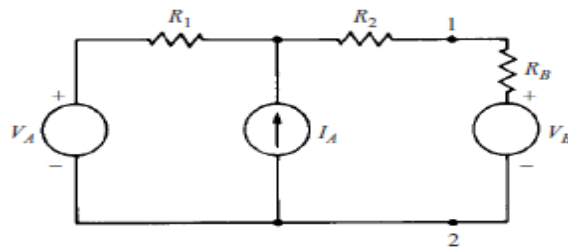


Fig.1

Answer:

Q.2

Q. With terminals 1-2 open circuited, no current flows through  $R_2$ , by using KVL

(2x3)  $V_{th} = V_{12} = V_A + I_A R_1 = 2 + (2 \times 4) = 10V$

$Z_{th}$  - With  $V_A$  replaced by a short and  $I_A$  replaced by an open circuit.

$Z_{th} = R_{th} = R_1 + R_2 = 4 + 3 = 7\Omega$

- b. Explain Duality. Obtain dual network for the circuit shown in fig.2.

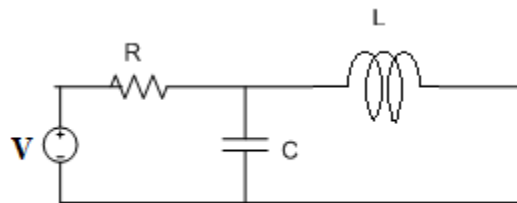


Fig.2

Answer:

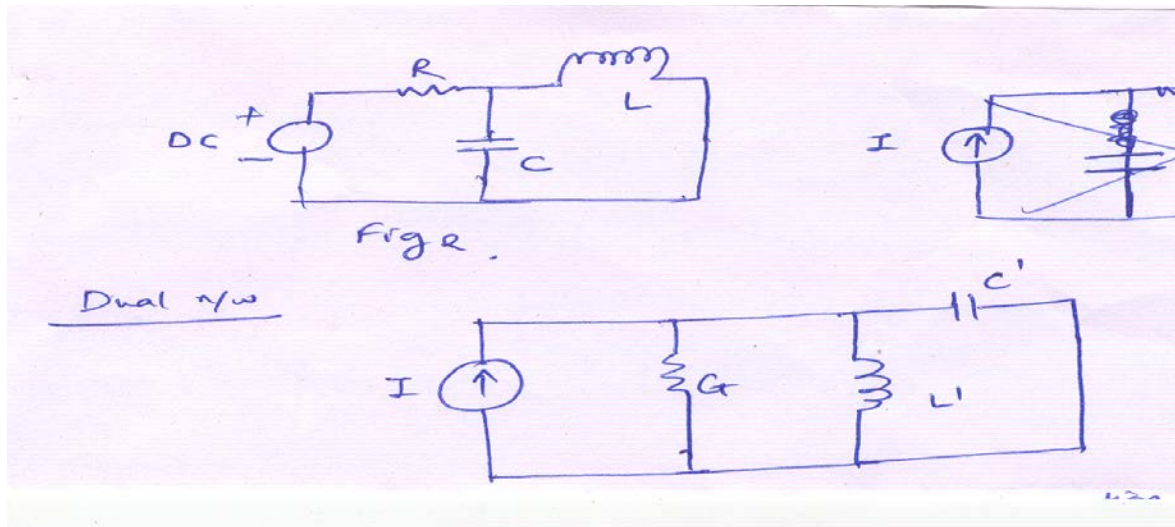
Duality :- Networks which have identical describing differential equations are known as dual of each other, and the concept is known as DUALITY.

eg. dual of elements

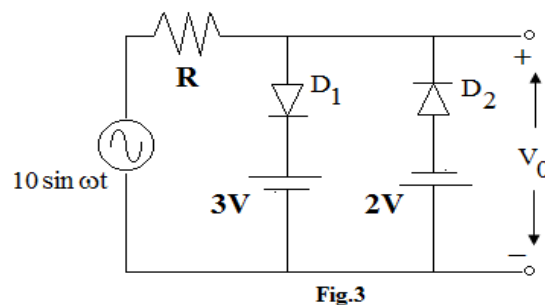
$R \leftrightarrow G$       voltage source  $\leftrightarrow$  current source,  
 $L \leftrightarrow C$

**Q.3** a. Draw and explain switching characteristics of a diode.

**Answer:**



b. Plot the output voltage  $V_0$



**Fig.3**

**Answer:** Topic 1.14 of Text Book 1

- c. Write short note on:
- (i) Transition and Diffusion capacitance
  - (ii) Zener diode as voltage regulator

**Answer:** Topic 1.13 of Text Book 1

**Q.4** a. Explain the construction and operation of a n-channel E-MOSFET with suitable diagram and characteristics.

**Answer:** Topic 2.3 of Text Book 1

- b. The transistor of Fig.4 is provided with the fixed and self biased emitter resistance with  $R_C = 4 \text{ k}\Omega$ ,  $R_E = 2 \text{ k}\Omega$ ,  $V_{CC} = 32 \text{ V}$  and  $I_C = 4 \text{ mA}$ .
- (i) Calculate the value of  $R_B$  if  $\beta = 100$
  - (ii) What will be the percentage change in  $I_C$  if actual  $\beta = 40$ ?

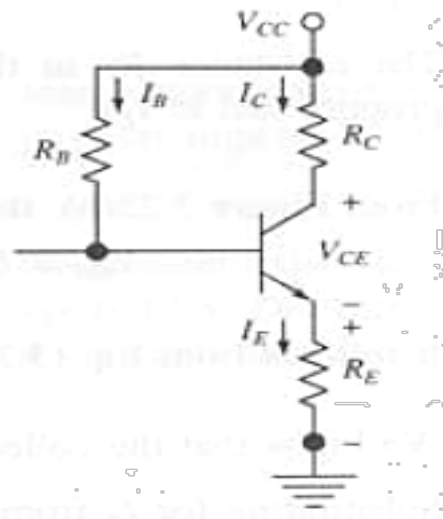


Fig. 4

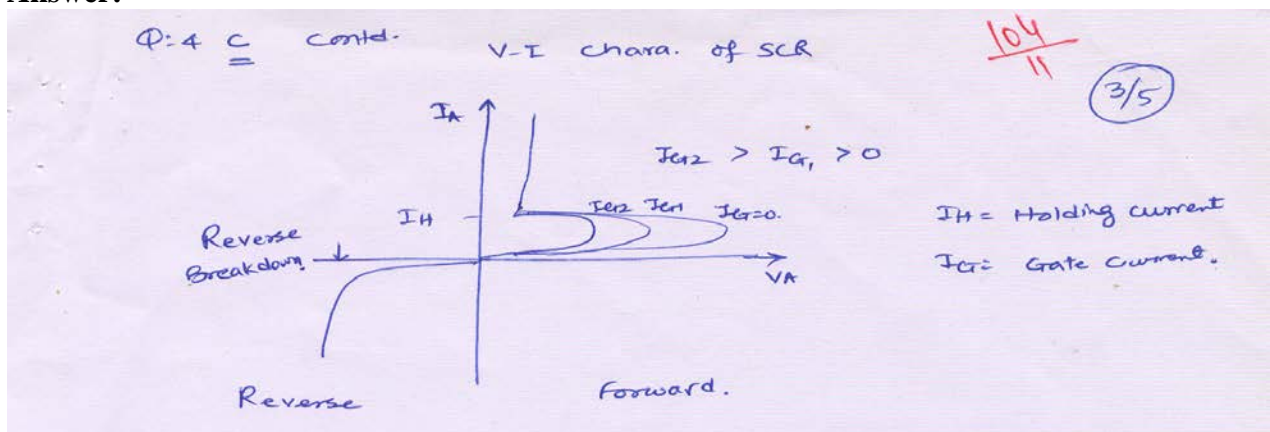
Answer:

Condition.	Emitter junction	Collector junction	Region of operation	Application
i) I FR	FB	RB	Active.	→ Amplification
ii) II FF	FB	FF	Saturation	→ Closed switch
iii) III RR	RB	RB	Cut-off	→ open switch
iv) IV RF	RB	FB	Inverted	→ Not used.

(∴ Very poor transistor action).

c. Draw V-I characteristics of an SCR.

Answer:



Q.5 a. Draw the small-signal model of Emitter follower and obtain the expression of voltage gain, current gain, input impedance and output impedance.



**Answer:**

Q.5  
(a) Given.  $R_C = 4\text{ k}\Omega$   $R_E = 2\text{ k}\Omega$   $V_{CC} = 32\text{ V}$  and  $I_C = 4\text{ mA}$

(i) Value of  $R_B$  if  $\beta = 100$ .  

$$I_B = \frac{I_C}{\beta} = \frac{4}{100} = 0.04\text{ mA}$$

$$V_{CC} = I_B R_B + V_{BE} + (I_B + I_C) R_E$$

$$32 = 0.04 \times R_B + 0.7 + (0.04 + 4) \times 2$$

$$\therefore R_B = 550\text{ k}\Omega$$

(ii) Actual  $\beta = 40$ ;  $A I_C = ?$   

$$32 = 550 I_B + 0.7 + (I_B + 4) \times 2$$

$$\therefore I_B = 0.04\text{ mA}$$

$$I_C = I_B \times \beta = 40 \times 0.04 = 1.6\text{ mA}$$

$$A I_C = 4 - 1.6 = 2.4\text{ mA}$$

$$= 60\% \text{ Reduction.}$$

b. Explain working of a Darlington pair amplifier in detail.

**Answer:** Topic 3.9 of Text Book 1

c. Write short note on CMOS.

**Answer:** Topic 3.2 of Text Book 1**Q.6** a. Explain working of tuned amplifier. Also state its merit and application.**Answer:** Topic 4.4 of Text Book 1b. A certain BJT transistor has  $r_\pi = 2\text{ k}\Omega$  and  $\beta = 50$  at  $1\text{ MHz}$  and  $\beta = 2.5$  at  $20\text{ MHz}$ . Determine  $f_T$ ,  $f_\beta$  and  $C_\pi$ .**Answer:**

(b) Given  $r_\pi = 2\text{ k}\Omega$  &  $\beta = 50$  at  $1\text{ MHz}$ .  
 $\beta = 2.5$  at  $20\text{ MHz}$ .

$f_T = \beta f_\beta = \beta_f \cdot f$   
 $f_T = 2.5 \times 20 = \underline{50\text{ MHz}}$

$f_\beta = \frac{f_T}{\beta} = \frac{50}{50} = \underline{1\text{ MHz}}$

$f_\beta = \frac{1}{2\pi C_\pi r_\pi}$   
 $1 \times 10^6 = \frac{1}{2\pi C_\pi 2 \times 10^3}$

$C_\pi = \frac{1}{2\pi \times 2 \times 10^3 \times 1 \times 10^6}$   
 $C_\pi = \underline{80\text{ pF}}$

c. Write short note on cascaded amplifiers.

**Answer:** Topic 4.6 of Text Book 1**Q.7** a. Compare Class A, Class B, Class AB and Class C power amplifiers.

Answer: Topic 5.5 of Text Book 1

- b. State performance parameters of power amplifier.

Answer:

i) Collector efficiency = ac power output / dc power input.  
 ii) Distortion -  
 iii) Power dissipation capability -

- c. A transistor supplies 2W for a 5 kΩ load. The zero-signal dc collector current is 35 mA and rises to 40 mA when signal is applied. Determine the percent second-harmonic distortion.

Answer:

③  $I_{C0} = 35 \text{ mA}$   
 $I_{C0} + B_0 = 40 \text{ mA}$   
 $\therefore B_0 = 40 - 35 = 5 \text{ mA}$   
 $P_1 = \frac{B_1^2 R_L}{2}$   
 $\therefore B_1 = 28.3 \text{ mA}$

$B_2 = B_0 = 5 \text{ mA}$   
 Second harmonic distortion.  
 $D_2 = \left| \frac{B_2}{B_1} \right| \times \frac{5}{28.3} \times 100$   
 $= 17.66\% \text{ Ans.}$

- Q.8 a. Define feedback. Which type of feedback is used for oscillator circuit? Discuss feedback's effect on input and output impedance.

Answer:

Q.8 (a)  
Feedback:- The process by which a fraction of output energy of device (amplifier) is injected back to its input is called feedback.  
 (01 mark)

Type:-  
 Positive feedback :- Used for oscillator circuit.  
 (01 mark) Negative feedback :- used for amplifier.

Rest Part:- Topic 6.4. Ret(F).

- b. A voltage series feedback amplifier has the following data:  $A = -500$ ,  $R_i = 1.5 \text{ k}\Omega$ ,  $R_o = 50 \text{ k}\Omega$  and  $\beta = (1/10)$ . Calculate amplifier gain, input and output resistances. Also draw topology for the same

**Answer:**

(2x3) ~~Q.9~~ (a) Given  $A = -500$ ,  $R_i = 1.5 \text{ k}\Omega$ ,  $R_o = 50 \text{ k}\Omega$  and  $\beta = 1/20$ . (2x4)

$1 + A\beta = 1 + 500 \times \frac{1}{20} = 26$

$A_f = \frac{-A}{1 + A\beta} = -\frac{500}{26}$

$A_f = 19.23$  amplifier gain.

$R_{if} = R_i (1 + A\beta) = 1.5 \times 26 = 39 \text{ k}\Omega$   
(input resi.)

$R_{of} = \frac{R_o}{1 + A\beta} = \frac{50}{26} = 1.92 \text{ k}\Omega$   
(output resi.)

Topology for voltage series feedback.

- Q.9** a. Write short notes:
- (i) Integrated resistors
  - (ii) Integrated capacitors

**Answer:** Topic 9.9 & 9.10 of Text Book 1

- b. State characteristics of IC components.

**Answer:** Topic 9.12 of Text Book 1

- c. State levels of integration of IC fabrication.

**Answer:** Topic 9.14 of Text Book 1

### TEXT BOOK

Electronic Devices and Circuits, I. J. Nagrath, PHI (2007)